2SC4680

Silicon NPN Epitaxial

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Application

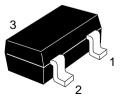
VHF / UHF high frequency switching

Features

- Low Ron and high performance for RF switch.
- Capable of high density mounting.

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



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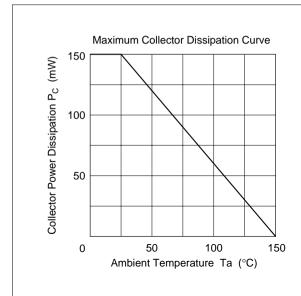
Absolute Maximum Ratings (Ta = 25°C)

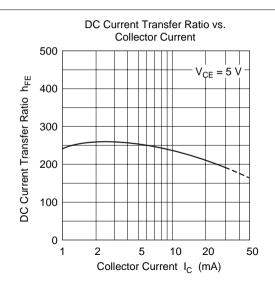
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

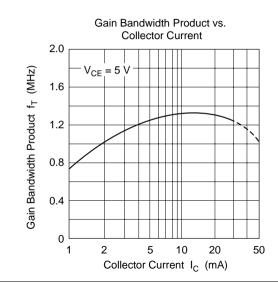
Electrical Characteristics ($Ta = 25^{\circ}C$)

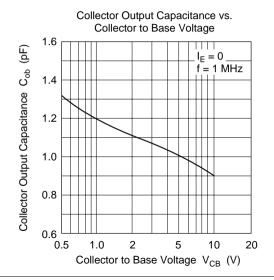
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	12	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 12 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	1	mA	$V_{CE} = 8 \text{ V}, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	_	_	10	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	70	100	mV	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$
DC current transfer ratio	h _{FE}	100	250	_		$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	1.0	1.5	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

Note: Marking is "XU-".

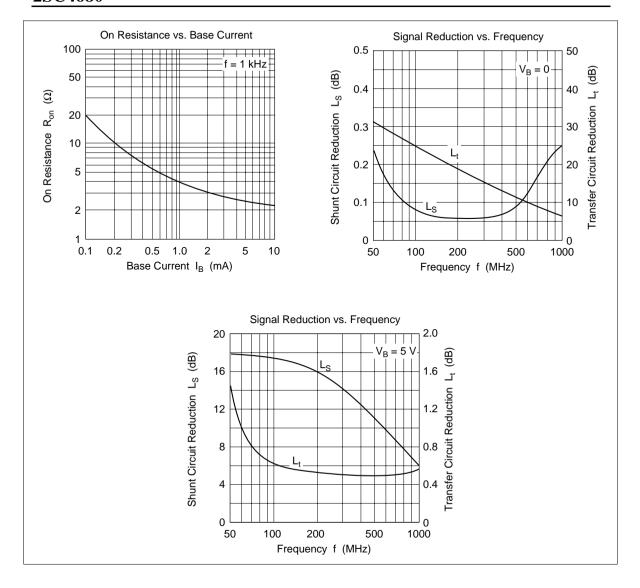




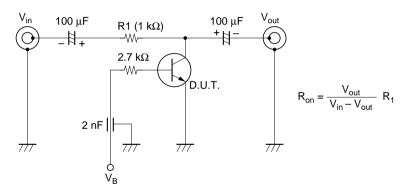




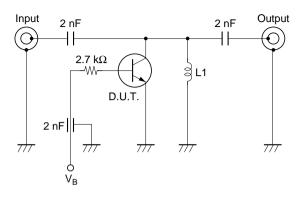
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On Resistance Test Circuit

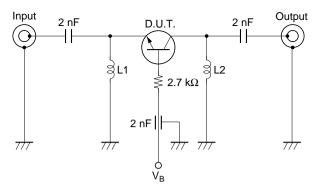


Reduction Test Circuit (Shunt Circuit)



L1 : 3 mm inside dia, ϕ 0.2 mm enameled copper wire, 15 turns

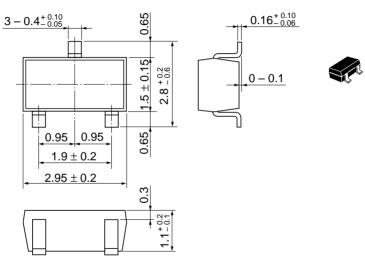
Reduction Test Circuit (Transfer Circuit)



L1, L2: 3 mm inside dia, ϕ 0.2 mm enameled copper wire, 15 turns

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Unit: mm



Hitachi Code	MPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.011 g

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